

L Number	Hits	Search Text	DB	Time stamp
20	4	((rie etch\$6) with (low adj temperature)) with ((below less) near (zero degree celsius))	USPAT; US-PGPUB	2004/06/25 17:21
21	63	(semiconductor wafer silicon substrate) and (pattern\$4 resist photoresist lithograph\$7 photolithograph\$7) and ((hole open\$4 aperture) same (taper\$3 isotropic\$6 slant\$4 angl\$4) same mask\$4 same ((organic flare silk polyimide) with (dielectric insulat\$4)))	USPAT; US-PGPUB	2004/06/25 17:27
22	142	(438/620.cc1s. 438/637.cc1s. 438/640.cc1s. 438/669.cc1s. 438/671.cc1s. 438/673.cc1s. 438/780.cc1s.) and ((semiconductor wafer silicon substrate) and (pattern\$4 resist photoresist lithograph\$7 photolithograph\$7) and ((hole open\$4 aperture) same (taper\$3 isotropic\$6 slant\$4 angl\$4) same mask\$4 same (organic flare silk polyimide dielectric insulat\$4)))	USPAT; US-PGPUB	2004/06/25 17:35
23	80	(pattern\$4 resist photoresist lithograph\$7 photolithograph\$7) and ((hole open\$4 aperture) with (taper\$3 isotropic\$6 slant\$4 angl\$4)) and mask\$4 and (organic flare silk polyimide)	EPO; JPO; DERWENT; IBM_TDB	2004/06/25 17:41
24	9	(dual adj hard adj mask) with organic	USPAT; US-PGPUB	2004/06/25 17:44
25	62	dual adj hard adj mask	USPAT; US-PGPUB	2004/06/25 17:46
26	11	5981913.URPN.	USPAT	2004/06/25 17:50
27	3757	438/620.cc1s. 438/637.cc1s. 438/640.cc1s. 438/669.cc1s. 438/671.cc1s. 438/673.cc1s. 438/780.cc1s.	USPAT; US-PGPUB	2004/06/25 17:51
28	811	(438/620.cc1s. 438/637.cc1s. 438/640.cc1s. 438/669.cc1s. 438/671.cc1s. 438/673.cc1s. 438/780.cc1s.) and (hole open\$4 aperture) and (taper\$3 isotropic\$6 slant\$4 angl\$4) and (mask\$4 resist photoresist)	USPAT; US-PGPUB	2004/06/25 17:52
29	0	6649517.URPN.	USPAT	2004/06/25 17:55
30	14	("4888087" "4978420" "5109267" "5786276" "5821141" "5915198" "6025259" "6037248" "6103619" "6114243" "6303498" "6369008" "6384480" "6448183" "2002/0031901").PN.	USPAT	2004/06/25 17:55